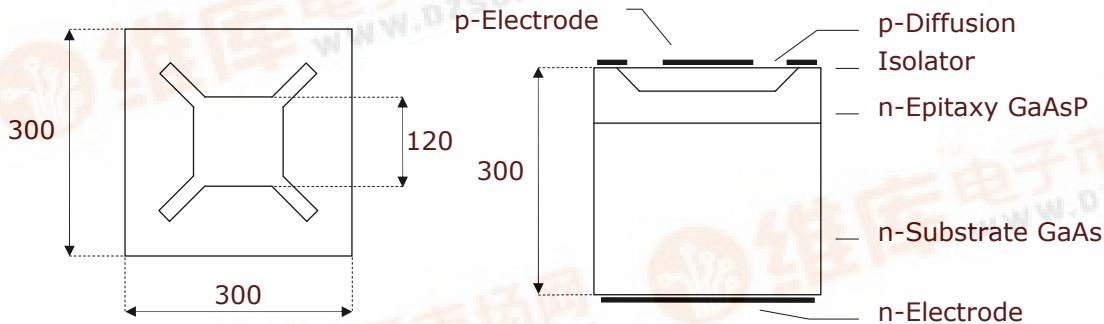


**RED**

**Item No.: 101205**

1. This specification applies to GaAsP / GaAs LED Chips
2. Structure
  - 2.1 Planar structure
  - 2.2 Electrodes
 

p-side (anode)	Al
n-side (cathode)	Au alloy
3. Outlines (dimensions in microns)



4. Electrical and optical characteristics (T=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Forward voltage	$V_F$	$I_F = 20 \text{ mA}$		1,65	1,84	V
Reverse voltage	$V_R$	$I_R = 10 \text{ }\mu\text{A}$	5			V
Luminous intensity *	$I_V$	$I_F = 20 \text{ mA}$	300	600		$\mu\text{cd}$
Peak wavelength	$\lambda_p$	$I_F = 20 \text{ mA}$		660		nm

\* On request, wafers will be delivered according to luminous intensity classes  
 Brightness measurement at OSA on gold plate

5. Packing
 

Dice on adhesive film with wire bond side on top
6. Labeling

Type	Lot No.	$I_V$ typ min max	Quantity